

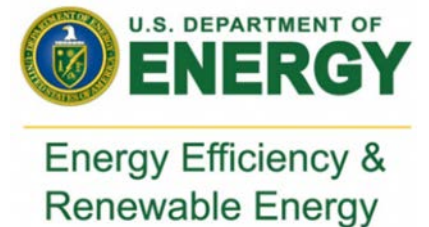
Conversion of solar photons into electricity: Silicon PV

Pauls Stradins

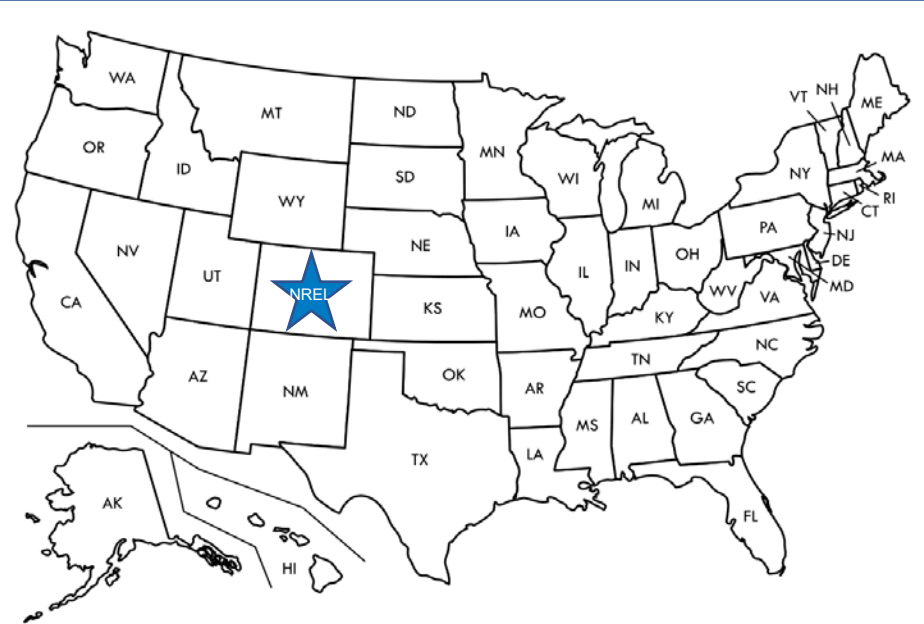
National Renewable Energy Laboratory,

Golden, Colorado USA

NREL/PR-5900-87583



The U.S. National Renewable Energy Laboratory



Our campus in Golden, Colorado



Dennis Schroeder

R&D Programs



Foundational Science

Materials Science

Biological Systems Science

Computational Science and Visualization

Renewable Power

Solar

Wind

Water

Geothermal

Energy efficiency

Buildings

Advanced Manufacturing

Sustainable Transportation

Bioenergy

Hydrogen and Fuel cells

Vehicles and Transportation Systems

Energy Systems Integration

Energy Storage

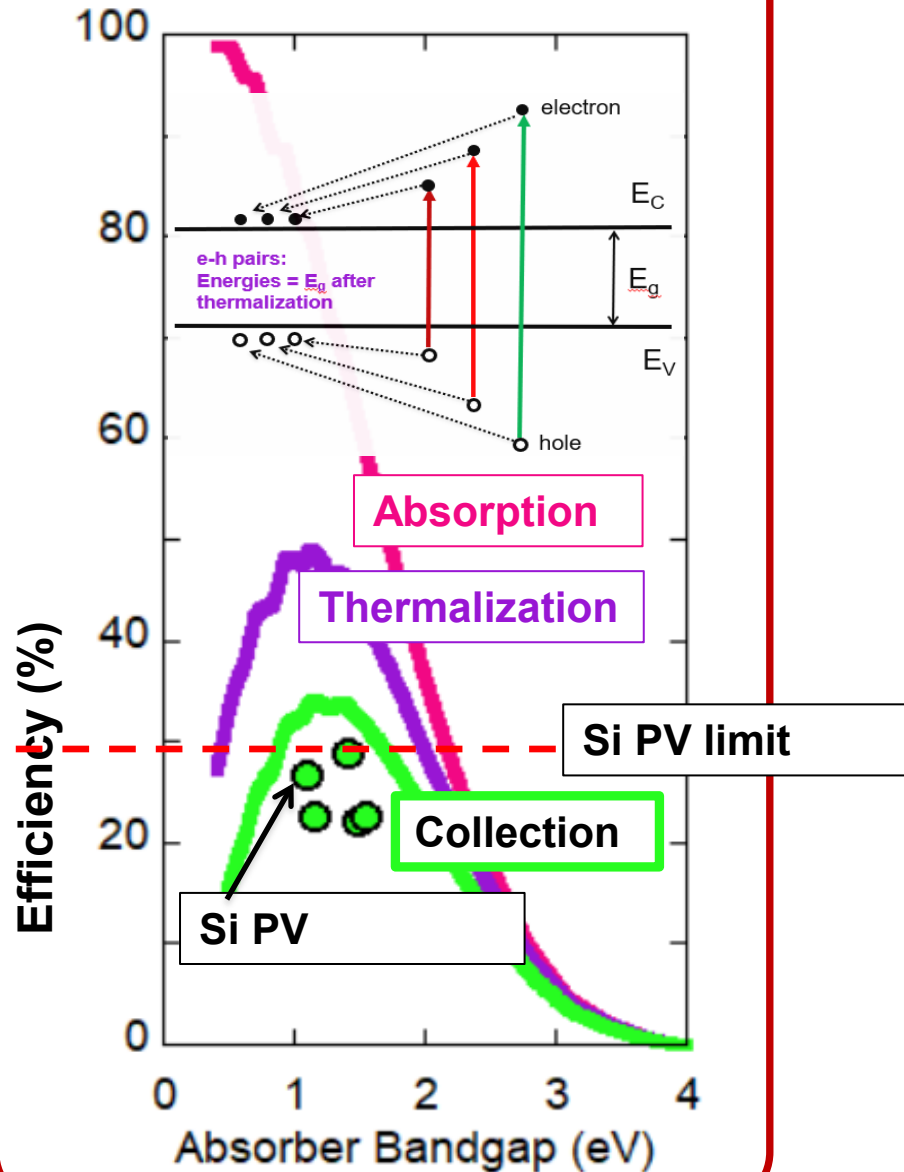
Grid modernization

Multipathway Systems Integration

Outline

- Solar energy rapidly becoming one of the dominant energy sources
- Silicon PV dominates and now massively expands to US manufacturing
- NREL Core Si PV team addresses main challenges of Si PV:
 - Efficiency: novel device architectures for next generation PV
 - Cost: industrially relevant, high throughput processes
 - Reliability: defects responsible for long-term performance loss

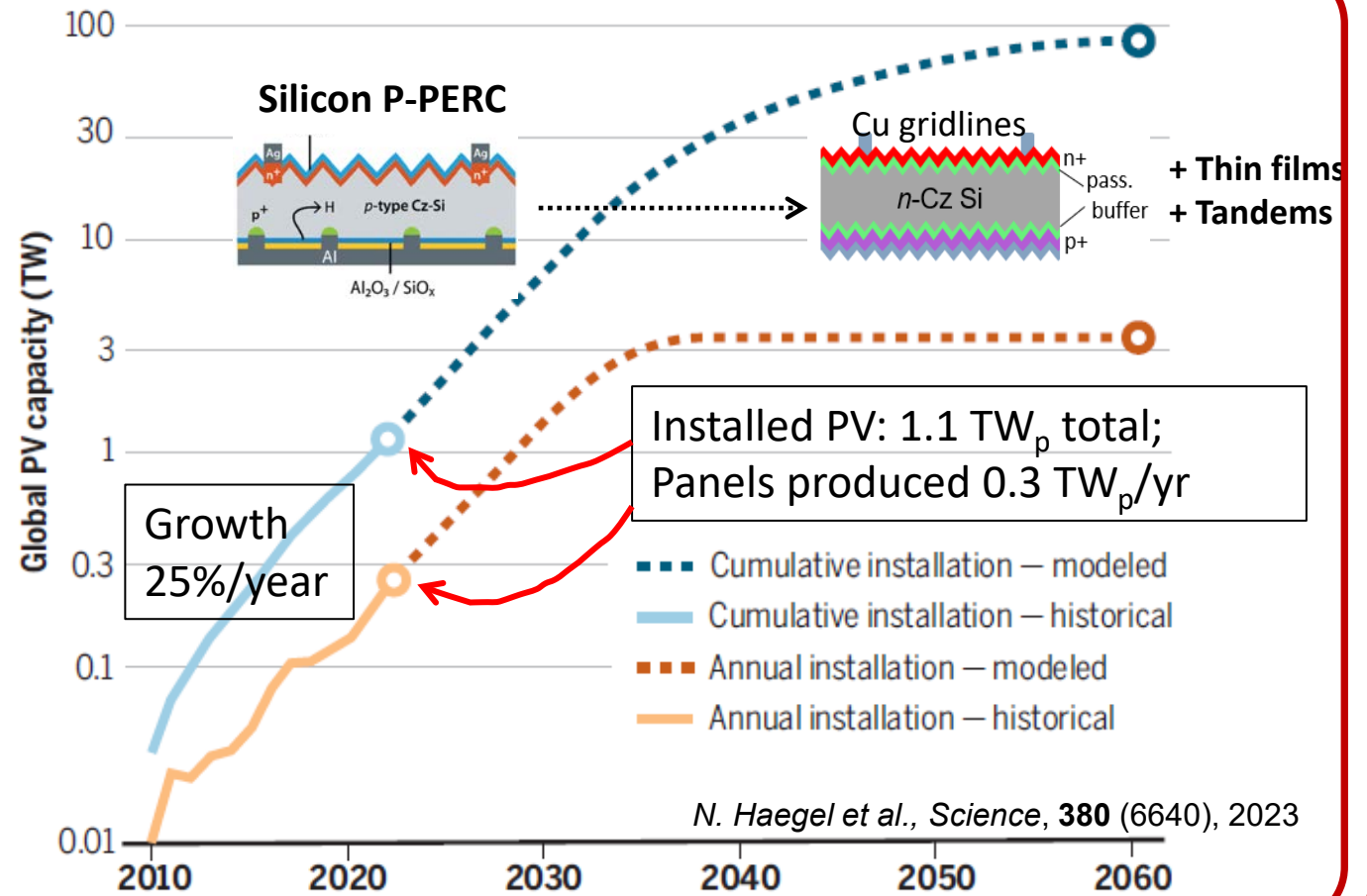
Fundamental efficiency limit:
single junction solar cell ~ 30%



Energy today:
(mostly fossil)

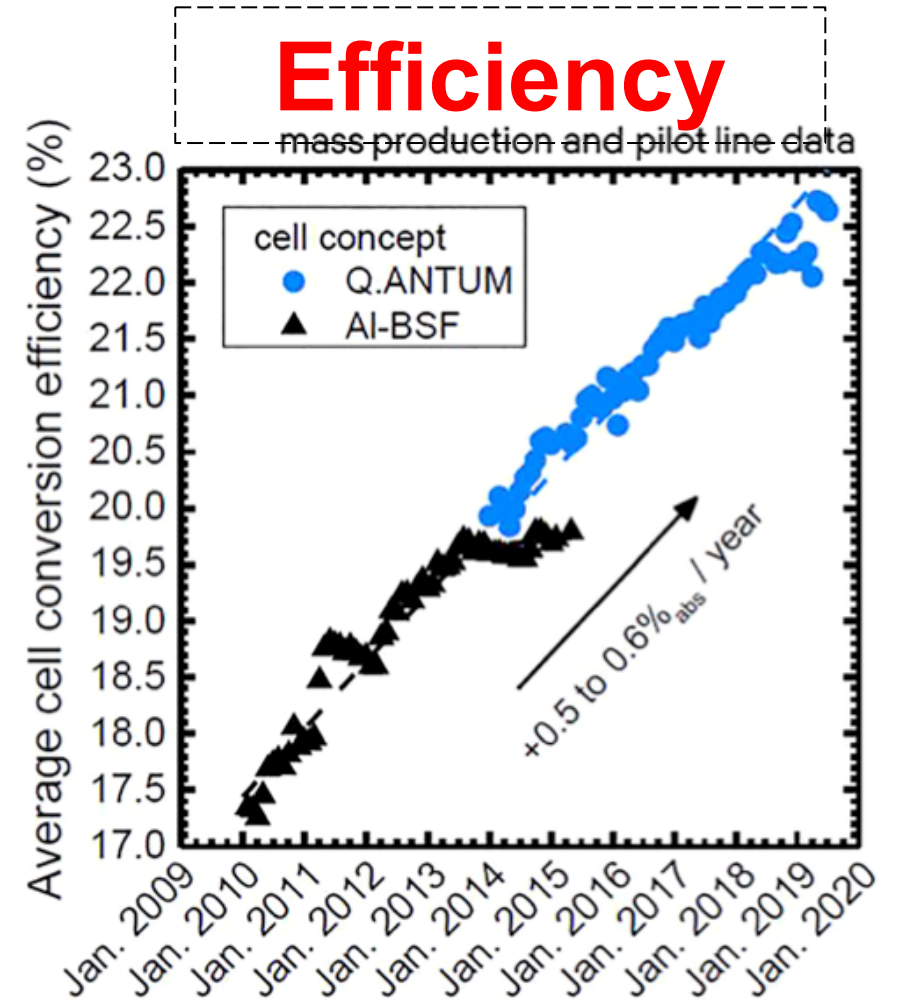
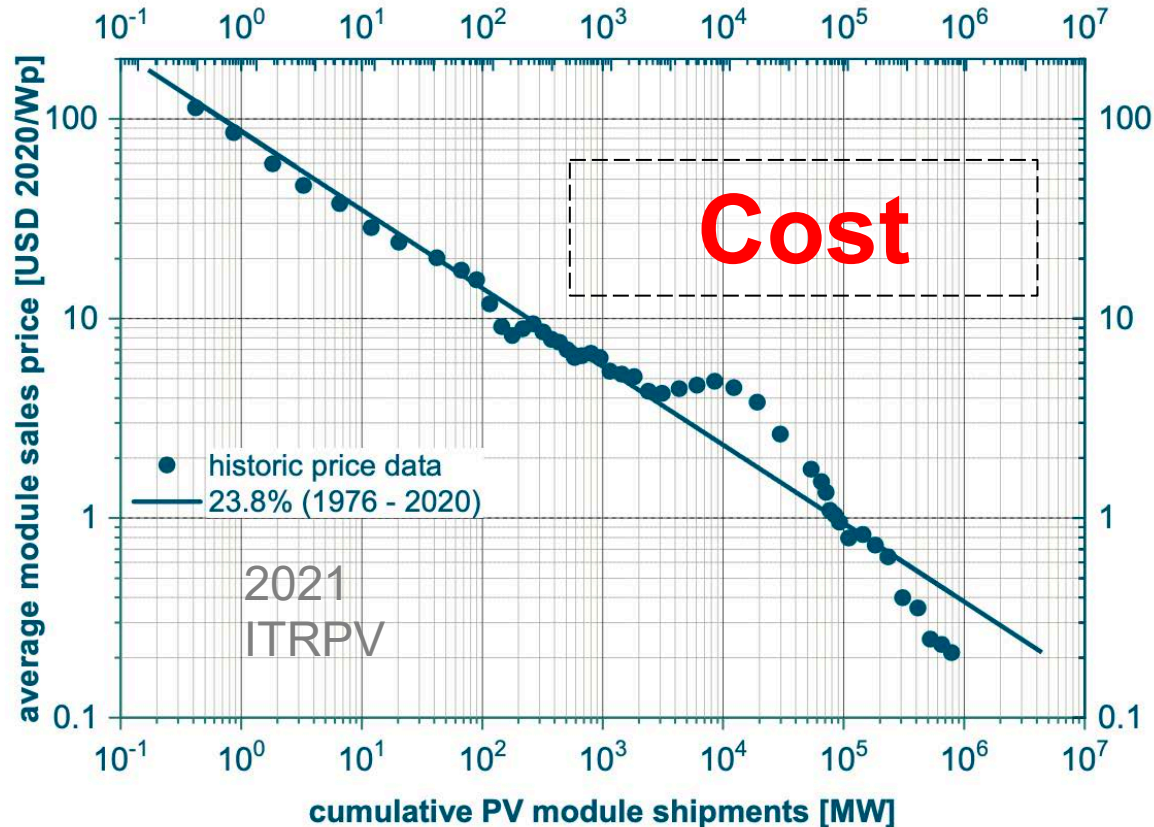
Primary energy consumption: 16 TW avg. power
Used for electricity generation: 6.8 TW
Electricity generated: 2.8 TW

Future with PV as the main energy source:



Si PV leads the PV world market at $\geq 95\%$; Efficiency rises $\sim 0.5\text{abs\%/year}$

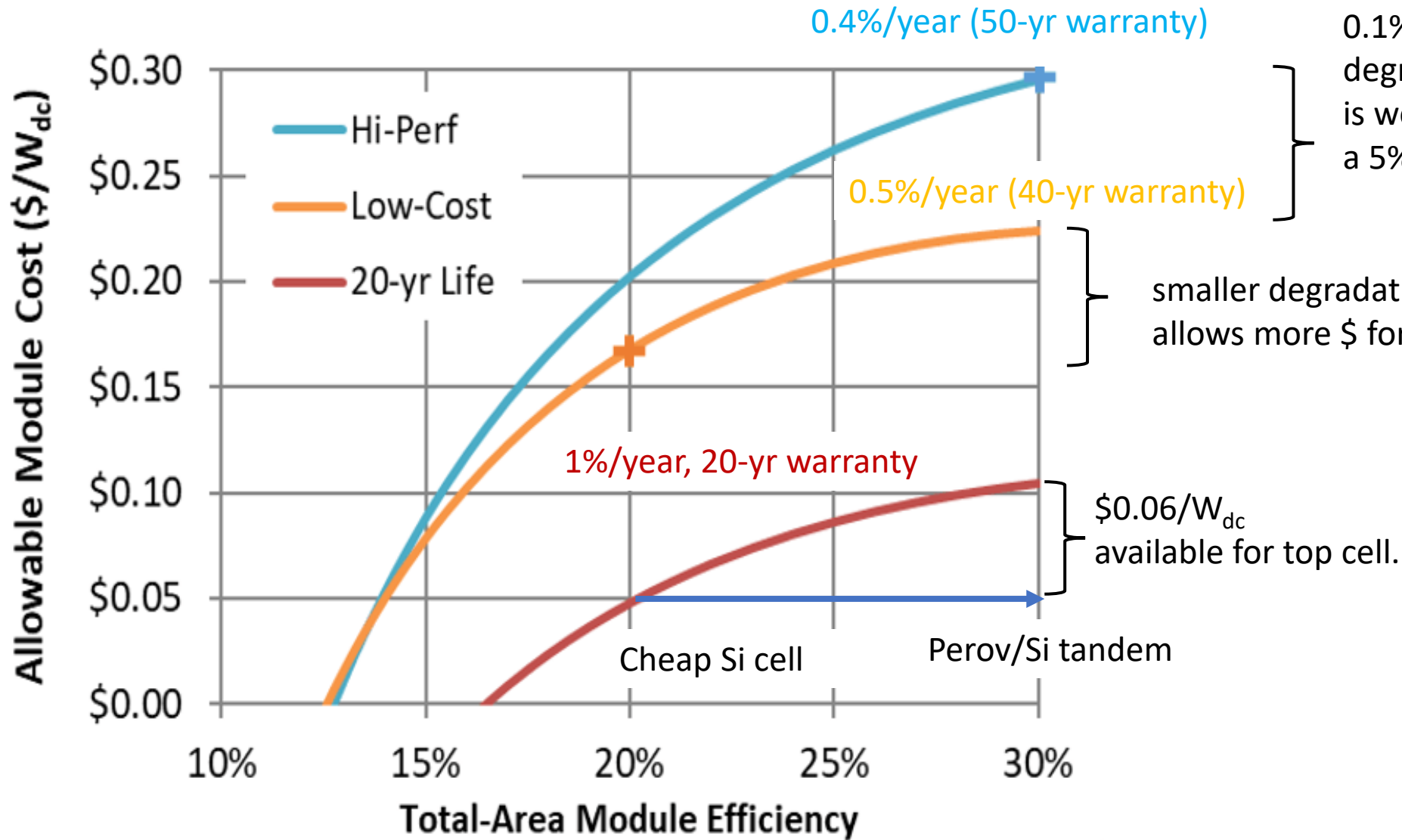
Learning curve for module price as a function of cumulative shipments



Fertig, F. et al., 2019 AsiaChem.

Silicon-based solar cells hold 95% of the world market share [2021 ITRPV].

LCOE (Cost, Efficiency, Reliability, CO₂, Energy, Recyclability, Equity) = \$0.02/ kWh

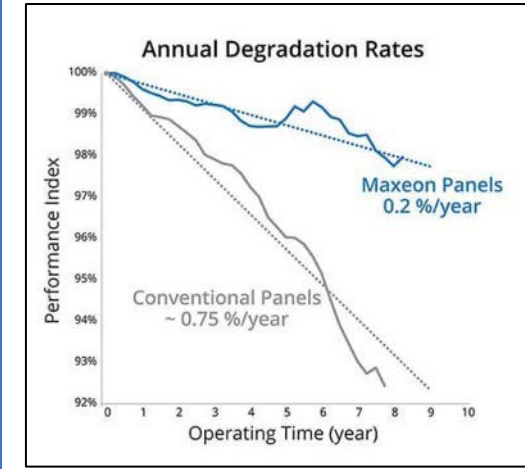


0.1% decrease in degradation rate is worth more than a 5% efficiency gain

smaller degradation rate allows more \$ for cells

\$0.06/W_{dc} available for top cell.

Maxeon/Sunpower: World record modules 40-year warranty



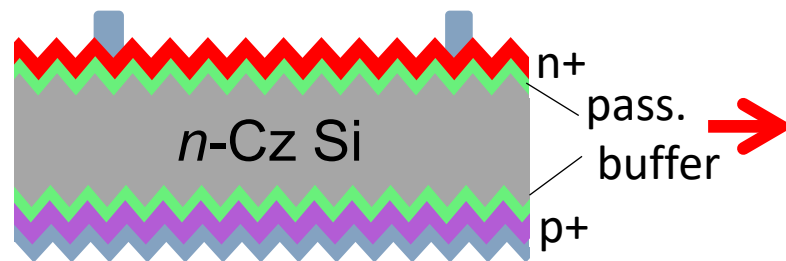
Silicon PV Evolution: approaching 29.4% efficiency limit

Future:

Passivated contact cell > 25%

Buffer = a-Si or tunnel SiO_2

High bulk lifetime, surface passivation, low-rec. contacts



Present: P-PERC

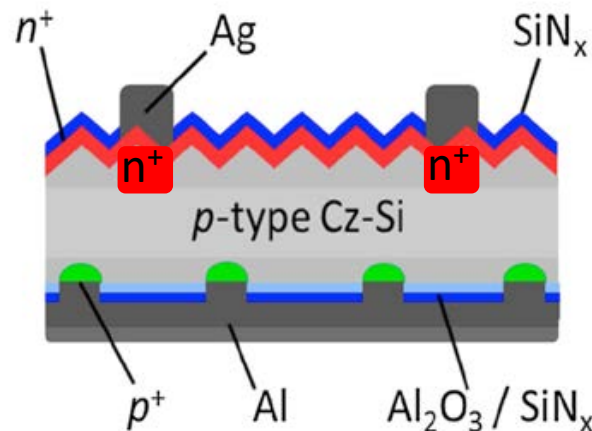
> 24% efficiency potential

Local Al-BSF ~ 1% area fraction

Selective front emitter

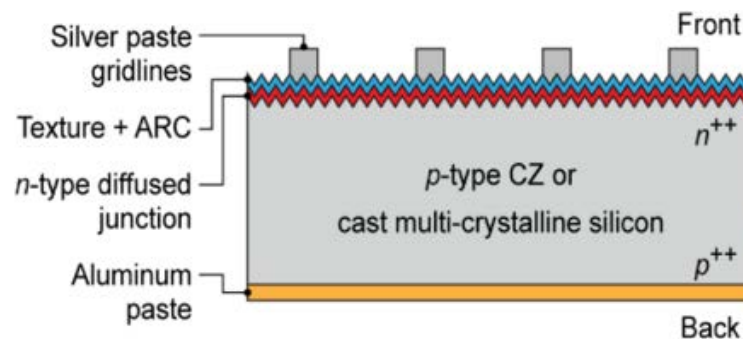
SP/metal recombination minimized

Can be bifacial

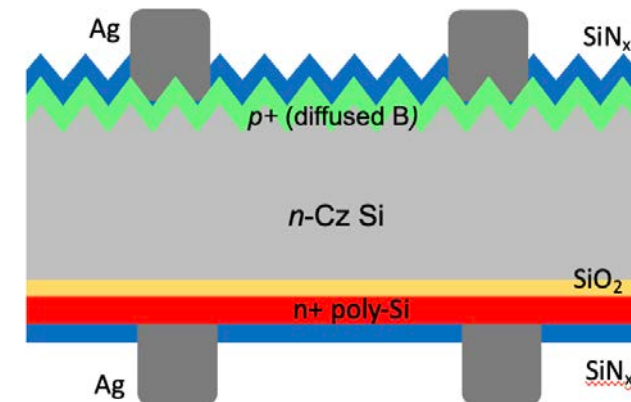


Al Back Surface Field cell, 20%

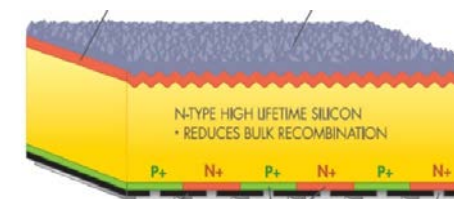
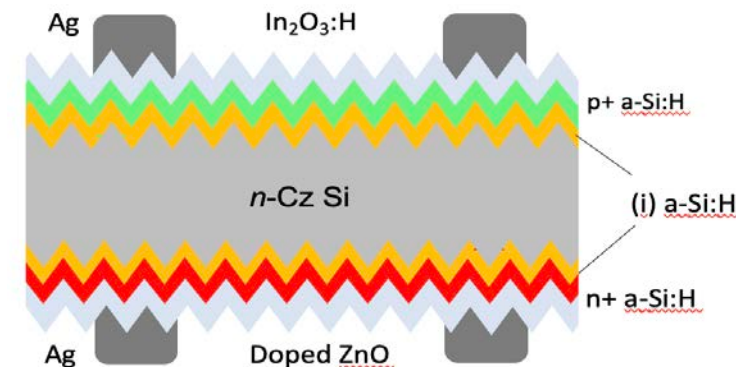
Al-diffused non-passivated BSF (high-low junction) limits efficiency



TOPCon cell 26% - less expensive

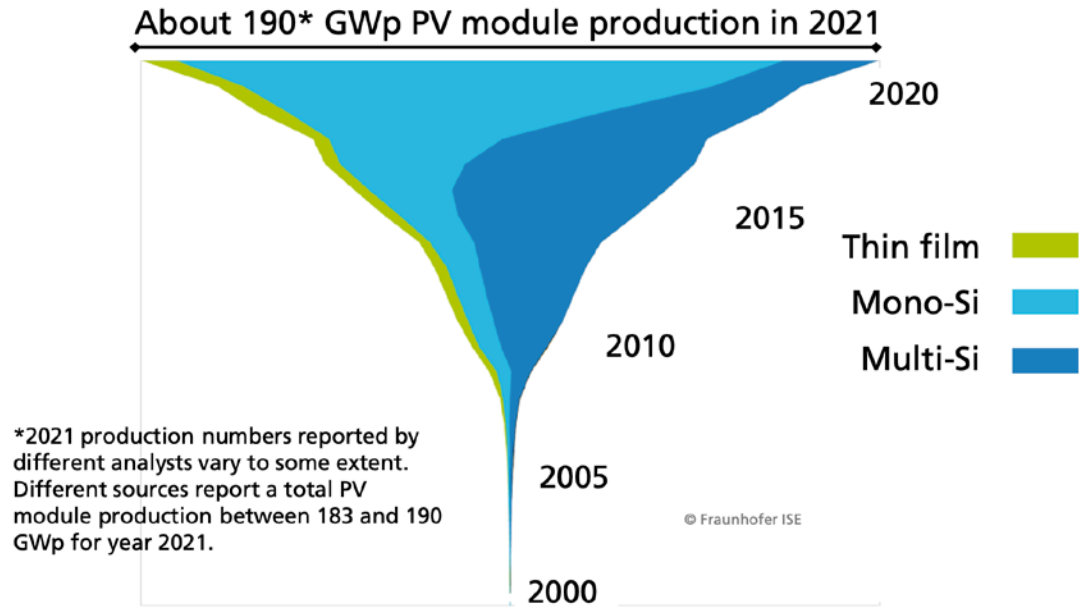


Silicon Heterojunction (SHJ) cell 27%

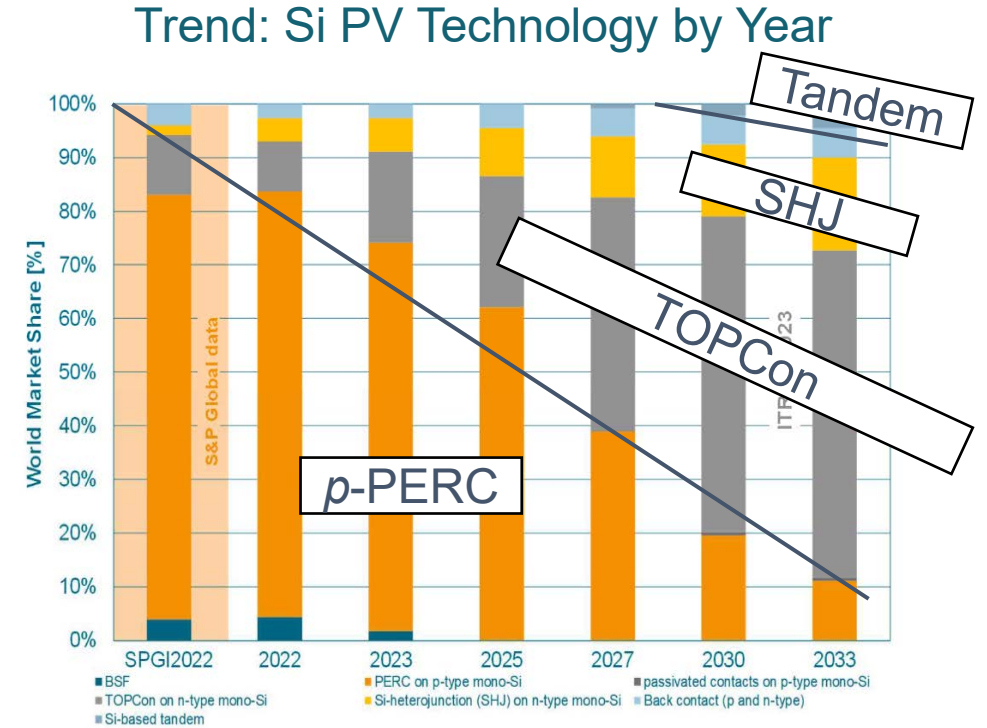


IBC cell

Evolution of Si PV Technologies: TOPCon taking over the PV market



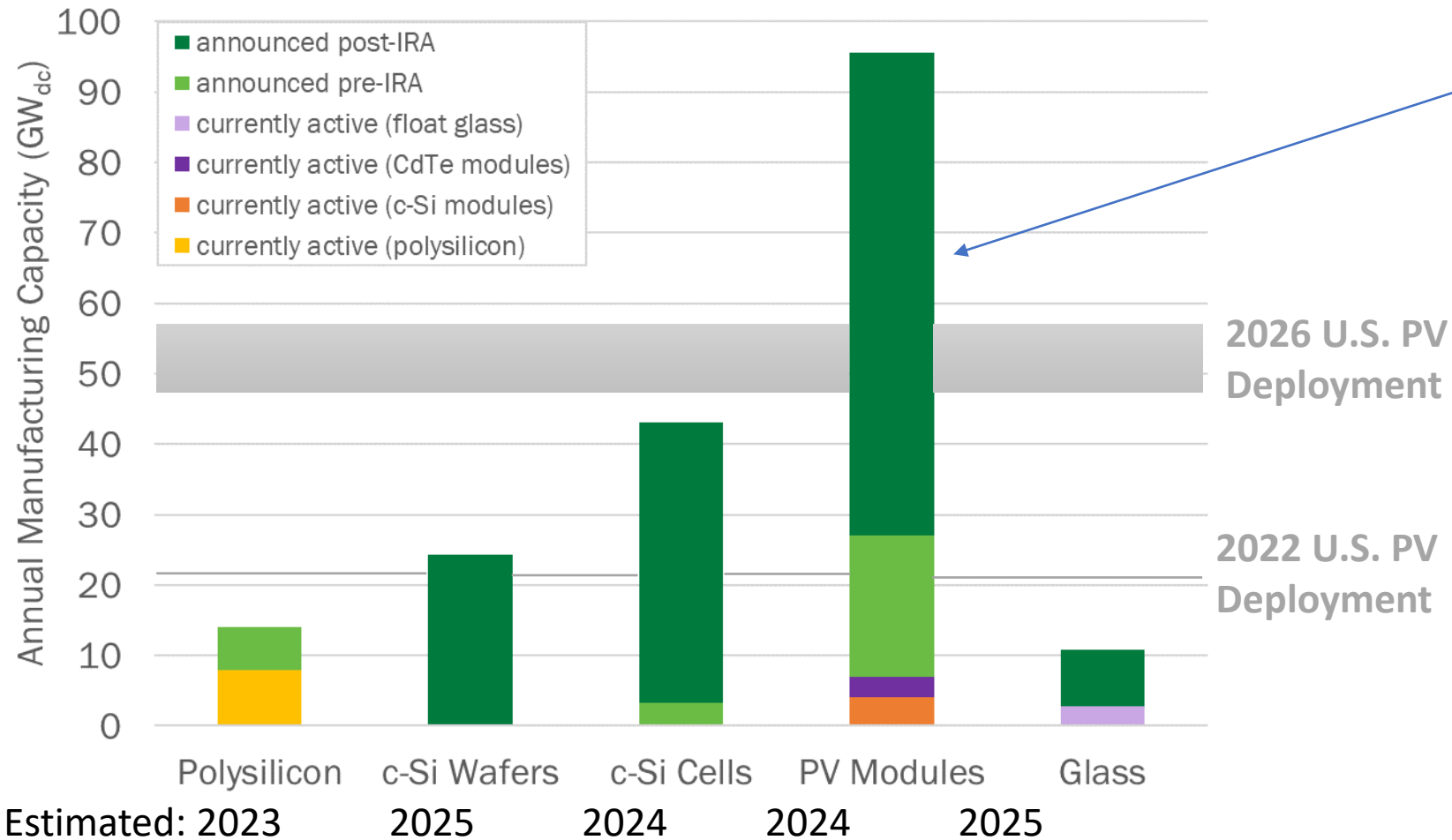
Source: Photovoltaic Report, Fraunhofer Institute for Solar Energy Systems; Feb 21, 2023



Reproduced from ITRPV 2022

- Solar energy is one of the fastest growing renewable energy markets
- c-Si occupies > 95% PV market with increasing *n*-type mono c-Si share

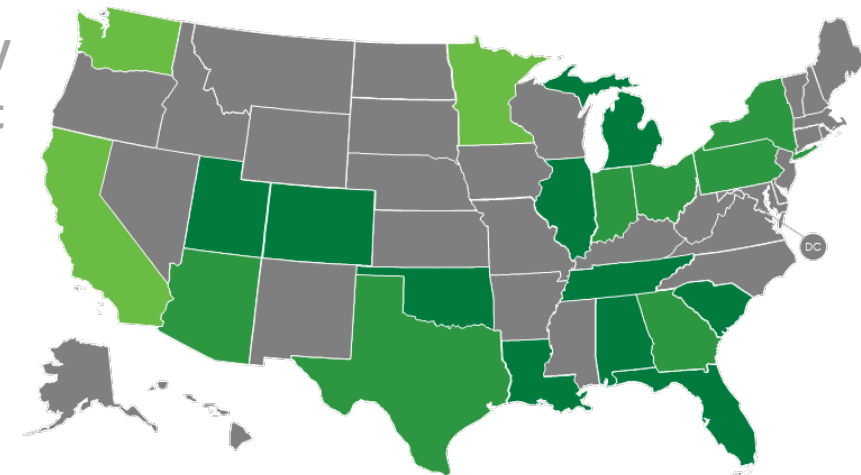
Anticipated Growth in US Solar Manufacturing Capacity: Value chain



Maxeon, Q-cells, Convalt, Enel

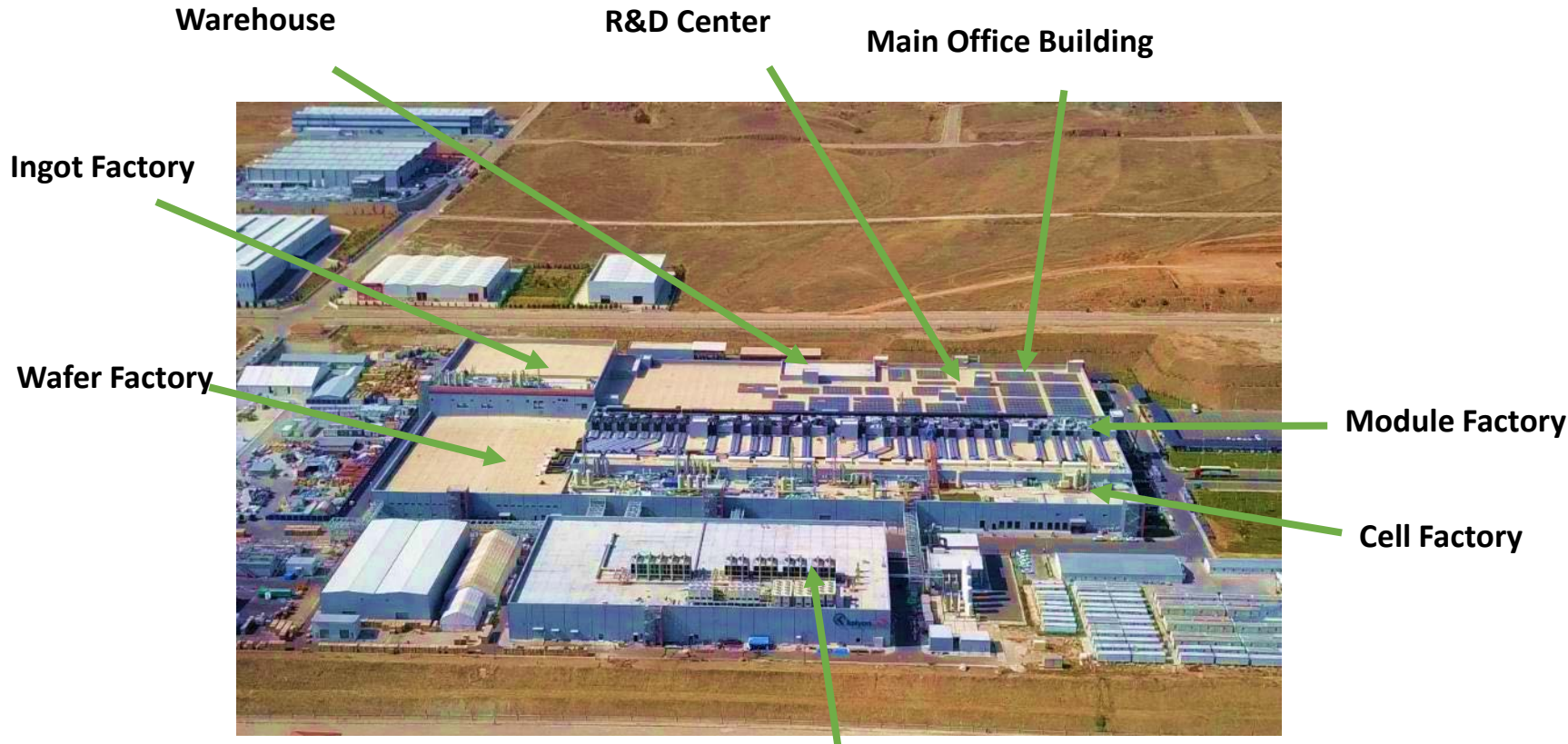
With IRA tax incentives, the United States is expected to have enough module production capacity to meet domestic demand, but many of the production tools, components, and materials will likely be imported

2022 U.S. PV Deployment



■ announced pre-IRA ■ announced post-IRA
■ mix of pre- and post-IRA

2.2 GW integrated (ingot-wafer-cell-module) factory in full operation since 2021



Areas	Total area (m ²)
Main building	ca. 80,000
Utility building	ca. 11,000
Waste water treatment	ca. 7,000
Others	ca. 3,000

25 Acres/2.2 GW

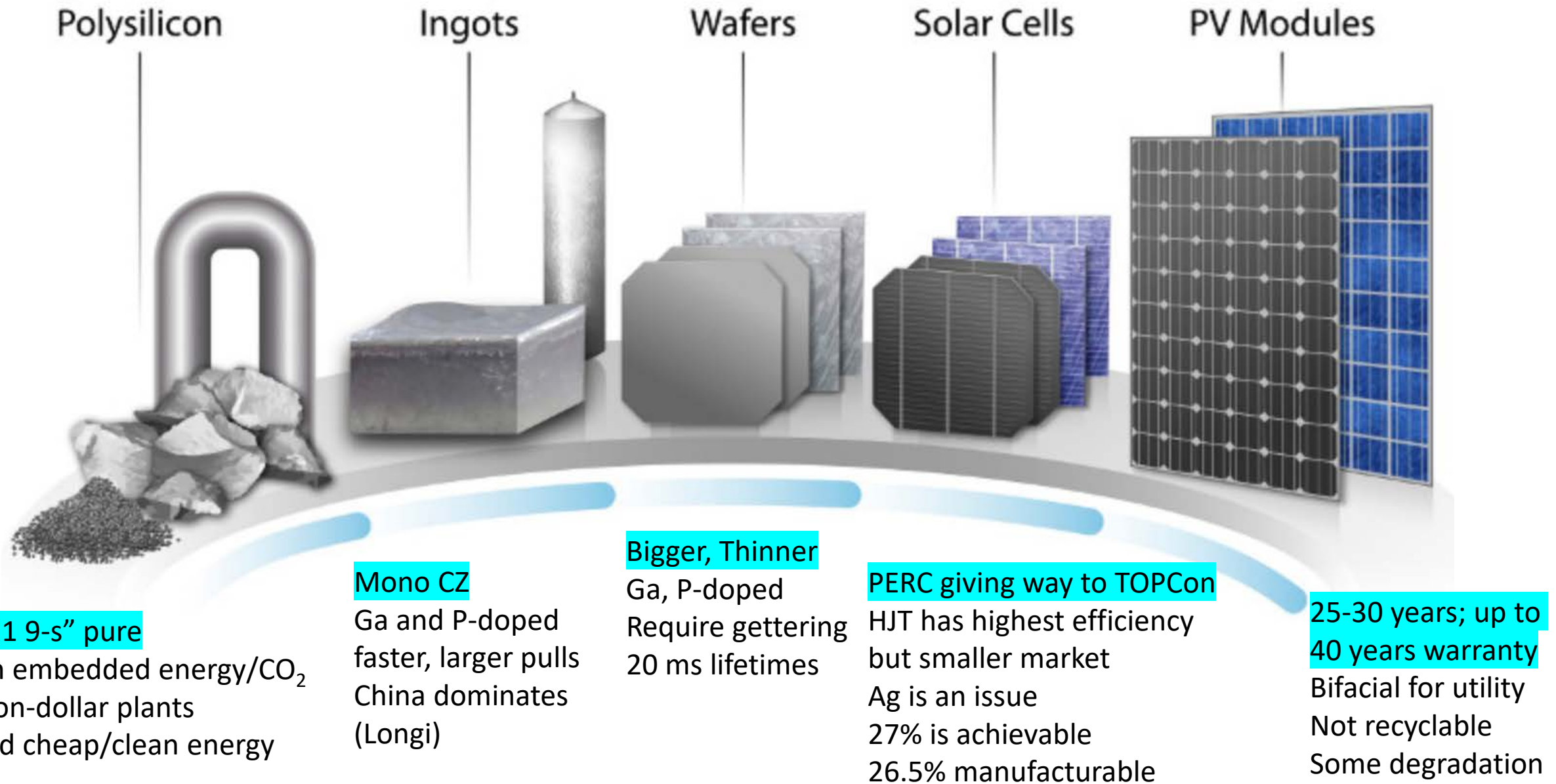
Utilities: Di Water, CDA, Special Gases and Bulk Gases

Ankara, Turkey

Mono PERC, bifacial

Si PV Factory built in 12 months

Thanks to Peter Fath, RCT solutions, for this slide



NREL Si Core Team Addresses Challenges of Si PV Technology

- **Efficiency:**

- Advanced passivated contacts to enable > 25% cells (excellent passivation and transport, ✓ transparent)
- High efficiency device architectures implementing passivated contacts ✓
- Very high bulk lifetime: perfect crystal growth, no process- or light induced defects ✓

- **Cost:**

- Low cost, Earth abundant metallization – Ag screen print (reduce >4x), replace with Cu ✓
- Replacing In in TCOs (for HJ cells) with other elements (only 3 nm ITO allowed)
- Low-cost cell architectures, few process steps ✓

- **Reliability:**

- No bulk degradation in p-Cz Si wafer bulk: LID, LeTID, no mechanism revealed ✓
- Mitigate Potential Induced Degradation (PID)
- No other degradation modes, even in n-Cz cells ✓

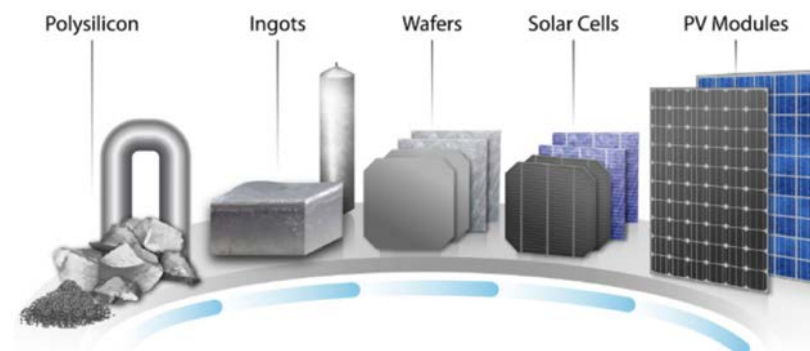
- **Recyclability:** modules (and kerf) ✓

- **Future** hybrid technologies: Si-based tandem ✓

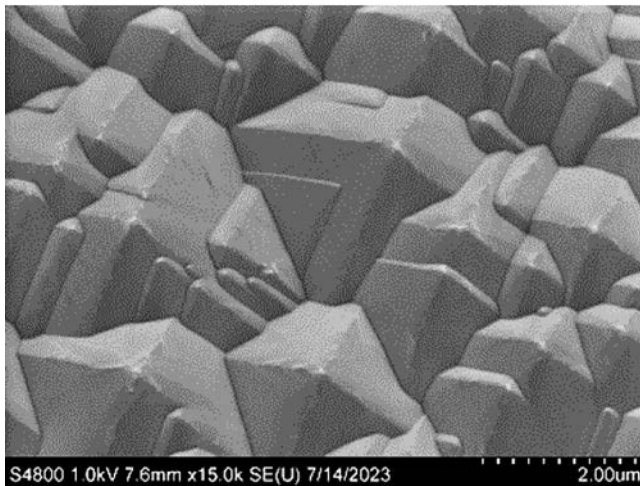
- ✓ Core expertise activity
- ✓ New recent activity

Silicon program at NREL: Main Achievements

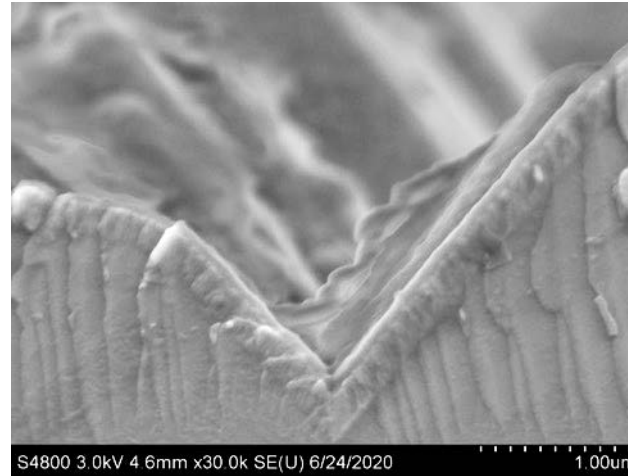
1. Introduced to mainstream Si PV, poly-Si passivated contacts with FhISE and GIT (2013 – 2015), now known as TOPCon cells, with global production outcompeting HJ cells.
 2. High-efficiency, stacked III-V/Si tandem cells (2015)
 3. Concepts of 3-terminal tandem cell and transparent conductive adhesive, IPs (2015); initiated stand-alone tandem program at NREL (2015)
 4. Bulk defect mitigation in n-Cz Si by *Tabula Rasa* (2014)
 5. Hydrogen passivation of poly-Si contacts by solid H source, IP (2014)
 6. Trap-assisted dopant compensation for IBC cells (2018 - 2020)
 7. Nickel silicide barrier stability for Cu metallization (2015- 2018)
 8. Si battery anode research - SEISTa consortium: role of oxide barrier, in situ surface-enhanced Raman (2017 – 2019)
 9. Electron Paramagnetic Resonance to reveal mechanisms of LID and LeTID degradation in mainstream p-Cz Si, and performance-degrading defect detection in n-Cz Si (2018 – present)
 10. Engineered nanopinhole contacts for high-efficiency Si cells, IP (2019 – present)
 11. Ga hyperdoping for passivated contact cells IP (2015 – present)
 12. New projects and industry collaborations on modules, Cu-metallization, poly-Si, power beaming, PhD level workforce for PV industry (2022, 2023)
- Licensed patent: Flash QE tester (2012) R&D100; 11 patents and applications; numerous inventions 2021-2023.



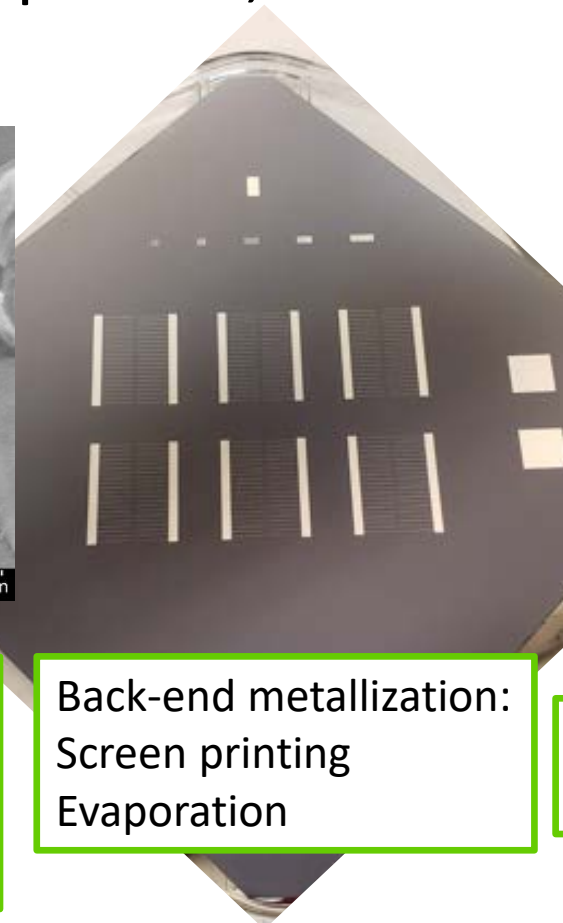
PV workforce training on the whole Si PV process, and new directions enabled with new cleanroom tools



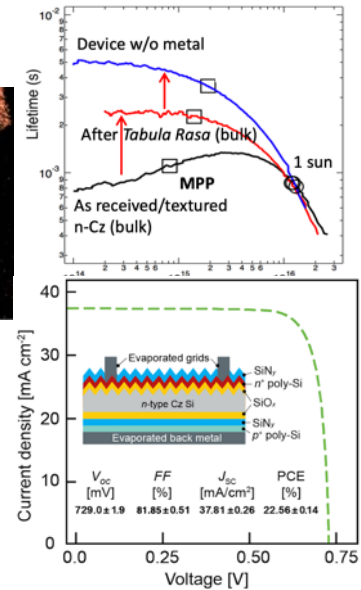
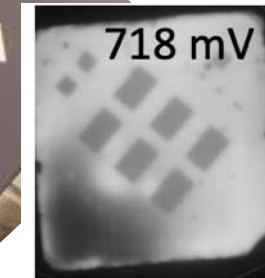
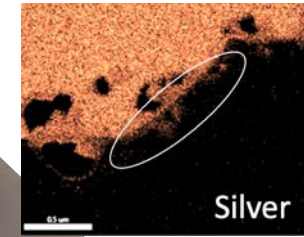
Front-end wet cleanroom chemistry (Singulus)



Depositions + Thermal (LPCVD, P, B, SiO₂, SiN_x – Tempress, Thermco; a-Si:H, ALD Al₂O₃ in cluster)



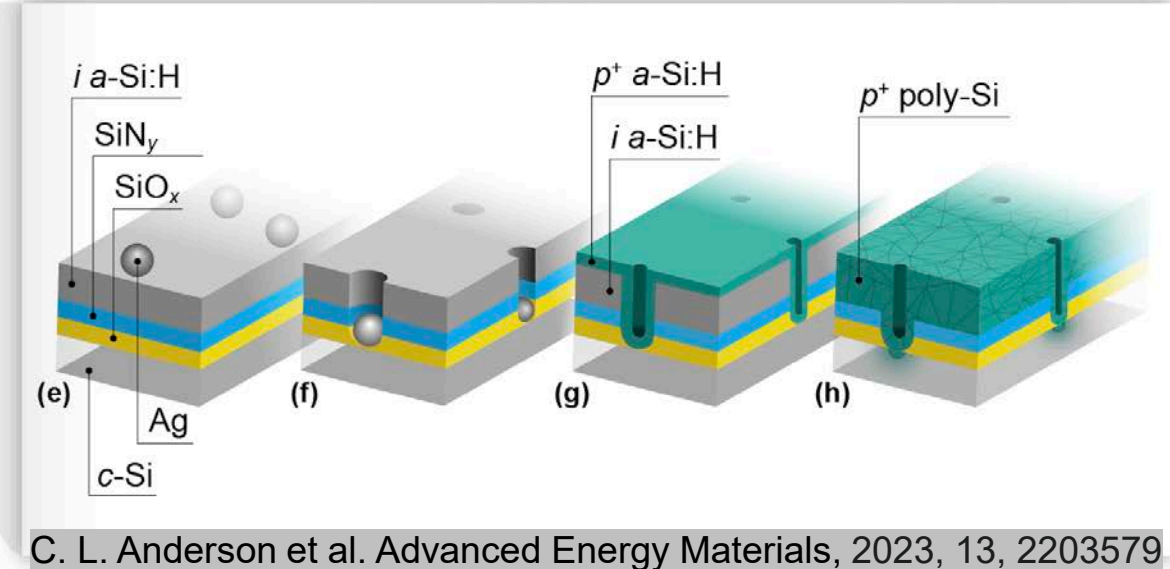
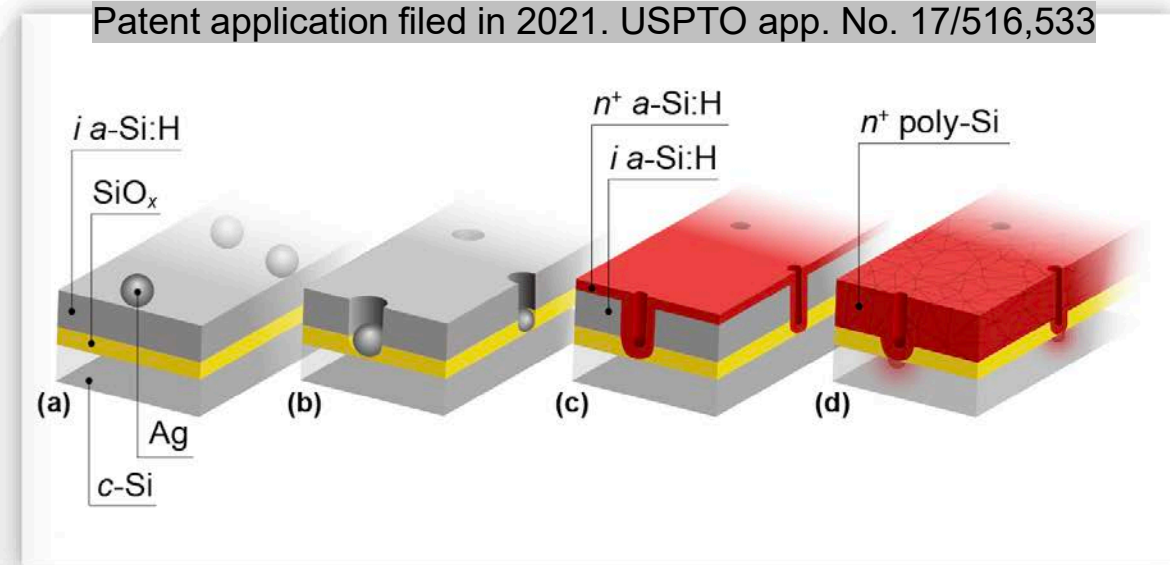
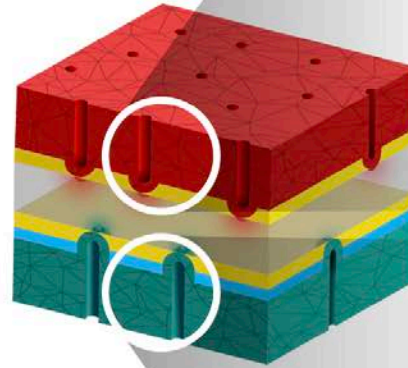
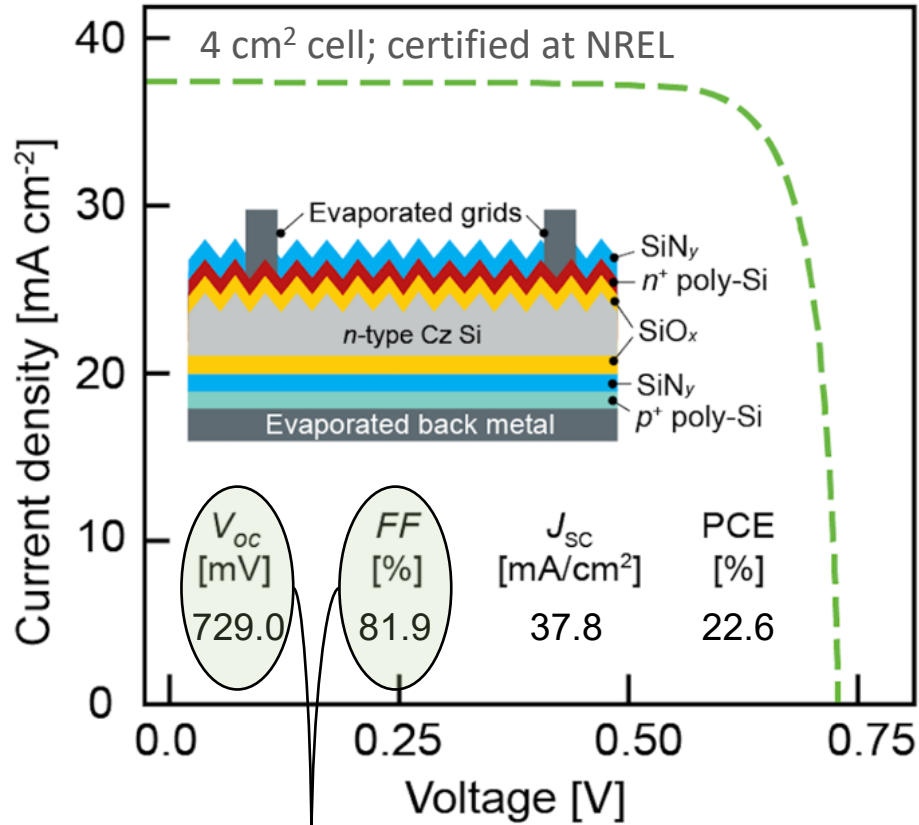
Back-end metallization: Screen printing Evaporation



Advanced Characterization: PL, Sinton, JV, QE, SEM, TEM, EBIC

- Next generation Si PV: novel passivated contacts, devices, reliability/defects, metallization (Ag to Cu)
- Industry engagement
- **Workforce training** on industrially relevant Si PV tools with highest cleanroom standards (students, engineers, interns)

Poly-crystalline silicon on locally etched insulators: electrical contacts for high-efficiency silicon solar cells



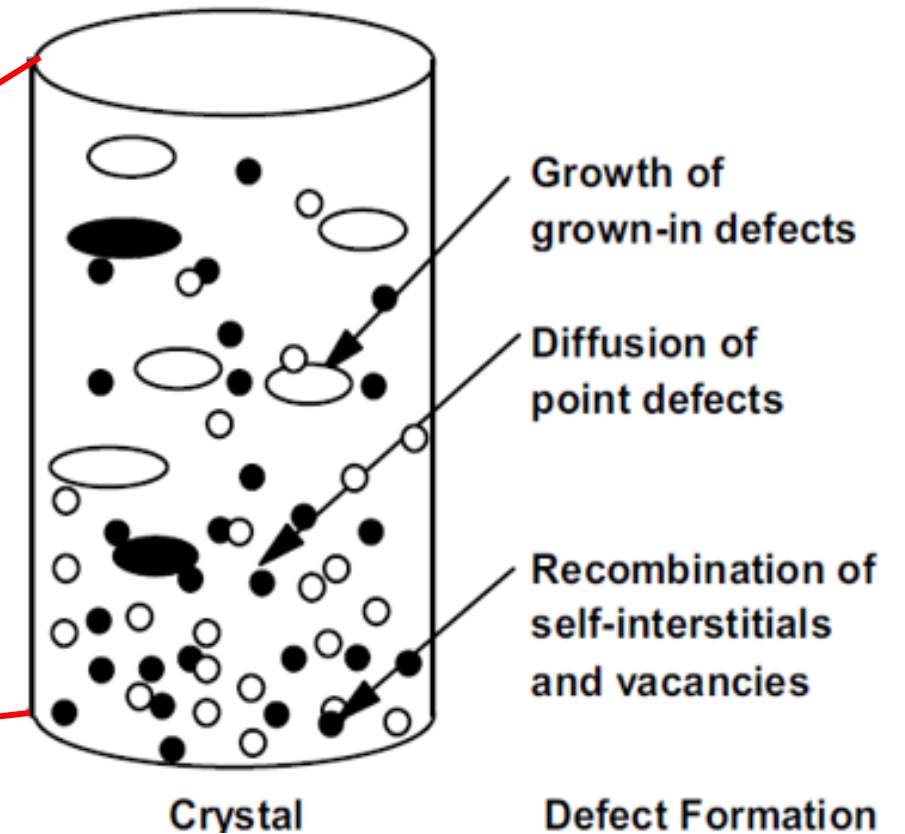
C. L. Anderson et al. Advanced Energy Materials, 2023, 13, 2203579
 note: few additional processing omitted for simplicity

- ❖ Insulating layers mitigate inherent surface defects, enabling high open-circuit voltage
- ❖ Within 1 cm², millions of nanoscale, conductive pathways enable current transport through insulating layers
- ❖ Area density of conductive pathways can be tuned, enabling solar cells with high open-circuit voltage and high fill-factor

The fabrication process applies galvanic corrosion principles to create nanoscale, conductive pathways

Today, most Si for electronics and PV is Cz–Si. The Cz growth process introduces small amounts of impurities and defects in the bulk.

NREL Si team: identify microscopic origins and mitigate these bulk defects.

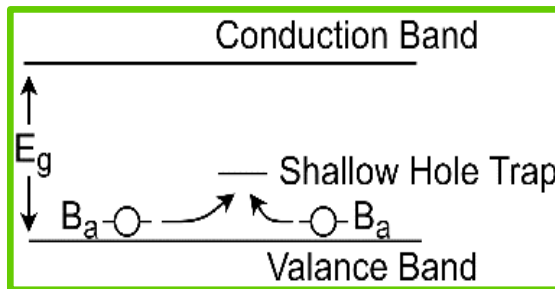
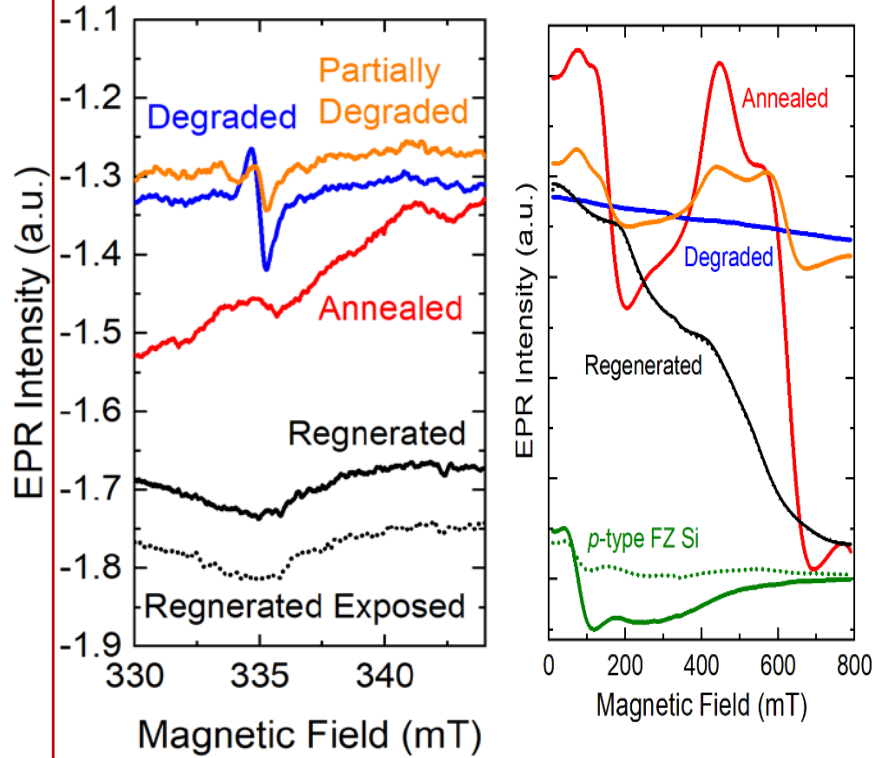


Dopants (P, B, Ga) – only partial segregation into solid.
Oxygen – solid solubility, precipitation with vacancies.
Metal impurities – self purification due to small $K_{segr} \sim 10^{-5}$

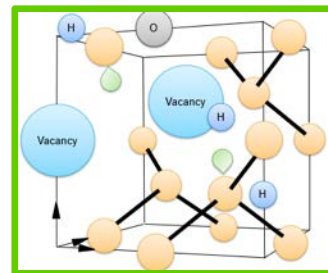
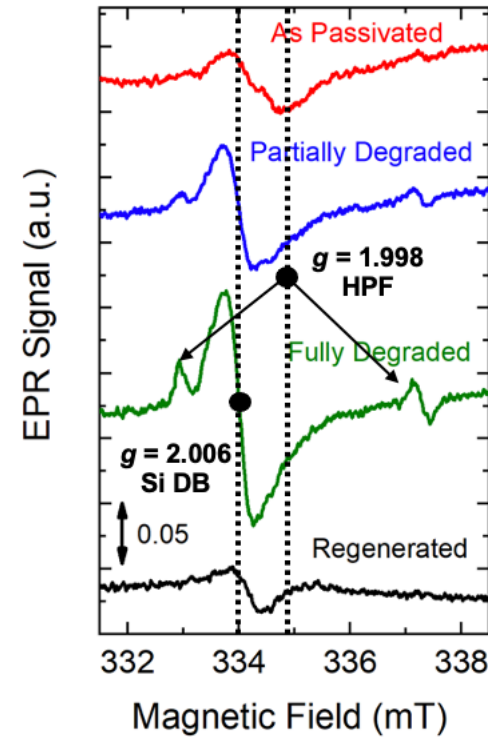
Fig. 1.2: Photograph of a silicon CZ puller with 200 mm crystal (Wacker Siltronic AG).

Electron Paramagnetic Resonance + EDMR for degradation mechanisms in p-Cz Si

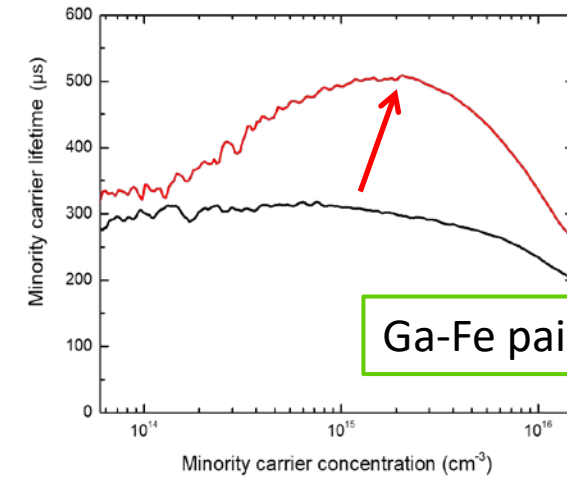
LID in Cz-Si:B – numerous, shallow hole traps created by light + deep defects



LeTID in Cz-Si:Ga Si
dangling bond in partially hydrogenated vacancy



Light-induced P-hyperfine signals in LeTID sample; DFT theory



Ga-Fe pair dissociation

Future Outlook

- NREL Si team's orientation towards high-quality science and innovation.
- Given the IRA support, a massive revival of Si PV across the whole value chain is expected in the next few years. We contribute to this by:
 - Industrially relevant innovative basic research addressing long term issues:
 - Cu metallization to replace Ag
 - Novel, industrially relevant passivated contacts (firable, transparent, nanopinhole)
 - EPR, EDMR, and electronic techniques for very low-level defect identification and mitigation
 - Expanded, wide-spectrum industry collaborations on shorter term issues:
 - Modern, flexible, compact baseline cell process capability at NREL for industry testing (*e.g.*, new wafers, device processes, Cu metallization)
 - Advanced characterization on ingot, wafer, cell, module level
 - Reliability - integrate cells with modules
 - Preparing the future industry leaders, PhD level workforce for the US PV industry.